









on the parameters of the crystal lattice of the formed graphite

Sample number	Initial state	Processing parameters P, T, т	a, Å	c, Å	B, at.%
1	Natural graphite	7.0ГПа, 1700 <sup>0</sup> С, 60sec	2.4622(3)	6.7181(30)	-
2	BC7	5.0ГПа, 1400 <sup>о</sup> С,	2 1611(1)	6 7055(6)	≈ 1

with the graphitization temperature increase.

Perfect graphene layer with 3% boron atoms

The peaks on the X-ray pattern of boron-doped graphite are not broadened, which reflects of a good periodicity of the Raman data can be solved by assuming that boron atoms are located in layers periodically and do not disturb the three-dimensional ordering.

Solid-state conversion of heavily boron doped graphite into heavily boron doped diamond occurs at a record low pressures of 7.5-8.0 GPa and temperatures of 1600-1650°C.

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